

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

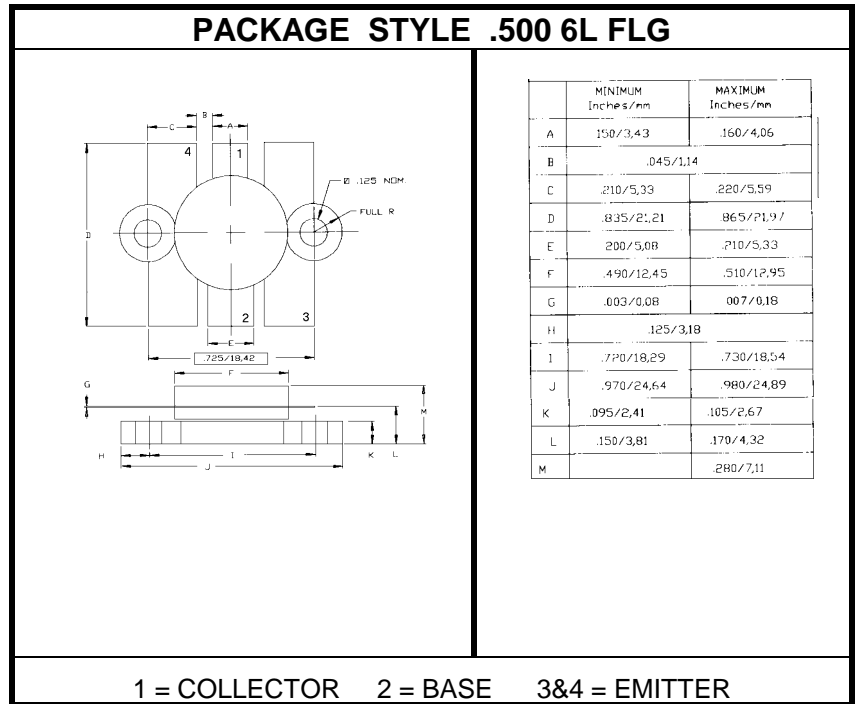
The **ASI BM100-28** is Designed for high power VHF Applications up to 200 MHz.

FEATURES:

- Common Emitter
- $P_G = 8.5$ dB at 20 W/175 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

| | |
|---------------|---|
| I_C | 20 A |
| V_{CEO} | 33 V |
| V_{CES} | 65 V |
| V_{EBO} | 4.0 V |
| P_{DISS} | 270 W @ $T_C = 25^\circ\text{C}$ |
| T_J | -65°C to $+200^\circ\text{C}$ |
| T_{STG} | -65°C to $+150^\circ\text{C}$ |
| θ_{JC} | 0.65°C/W |


CHARACTERISTICS $T_C = 25^\circ\text{C}$

| SYMBOL | TEST CONDITIONS | | MINIMUM | TYPICAL | MAXIMUM | UNITS |
|-------------------|------------------|-------------------|---------|---------|---------|---------|
| BV_{CEO} | $I_C = 50$ mA | | 33 | | | V |
| BV_{CES} | $I_C = 100$ mA | | 65 | | | V |
| BV_{EBO} | $I_E = 5.0$ mA | | 4.0 | | | V |
| h_{FE} | $V_{CE} = 5.0$ V | $I_C = 1.0$ A | 10 | | | --- |
| C_{CB} | $V_{VB} = 28$ V | $f = 1.0$ MHz | | 200 | | pF |
| P_G η_C | $V_{CC} = 28$ V | $P_{OUT} = 100$ W | 8.5 | 60 | | dB % |